

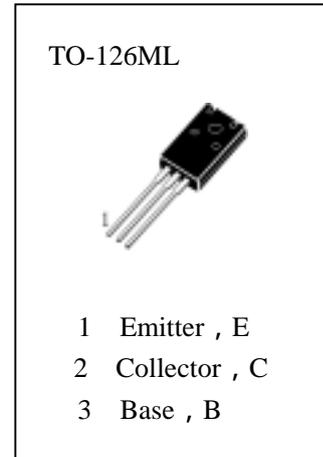


H649A

LOW FREQUENCY POWER AMPLIFIER

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation ($T_c=25$)	20W
P_C	Collector Dissipation ($T_A=25$)	1W
V_{CBO}	Collector-Base Voltage.....	-180V
V_{CEO}	Collector-Emitter Voltage.....	-160V
V_{EBO}	Emitter-Base Voltage.....	-5V
I_C	Collector Current (DC)	-1.5A



Electrical Characteristics ($T_a=25$)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
$H_{FE} (1)$	DC Current Gain	60		200		$V_{CE} = -5V, I_C = -150mA$
$H_{FE} (2)$		30				$V_{CE} = -5V, I_C = -500mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-1	V	$I_C = -500mA, I_B = -50mA$
BV_{CBO}	Collector-Base Breakdown Voltage	-180			V	$I_C = -1mA, I_E = 0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-160			V	$I_C = -10mA, I_B = 0$
BV_{EBO}	Emitter- Base Breakdown Voltage	-5			V	$I_E = -1mA, I_C = 0$
I_{CBO}	Collector-Base Cutoff Current			-10	μA	$V_{CB} = -160V, I_E = 0$
f_T	Current Gain- Bandwidth Product		140		MHz	$V_{CE} = -5V, I_C = -150mA$
C_{ob}	Output Capacitance		27		pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

h_{FE} Classification

B	C
60—120	100—200